Silicon PNP Power Transistors 2SA985 2SA985A

DESCRIPTION

- With TO-220 package
- Complement to type 2SC2275/2275A
- High breakdown voltage

APPLICATIONS

- For low frequency and high frequency power amplifer applicatons

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

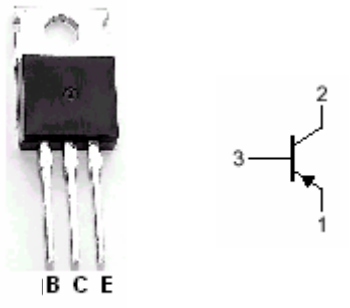


Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SA985	Open emitter	-120	V
		2SA985A		-150	
V_{CEO}	Collector-emitter voltage	2SA985	Open base	-120	V
		2SA985A		-150	
V_{EBO}	Emitter-base voltage		Open collector	-5	V
I_C	Collector current			-1.5	A
I_{CM}	Collector current-peak			-3.0	A
I_B	Base current			-0.3	A
P_T	Total power dissipation		T_a=25℃	1.5	W
			T_C=25℃	25	
T_j	Junction temperature			150	℃
T_{stg}	Storage temperature			-55~150	℃

Silicon PNP Power Transistors 2SA985 2SA985A

CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	2SA985	I_C=-25mA ,I_B=0	-120			V
		2SA985A		-150			
V_{CEsat}	Collector-emitter saturation voltage		I_C=-1A; I_B=-0.1A		-0.3	-2.0	V
V_{BEsat}	Base-emitter saturation voltage		I_C=-1A; I_B=-0.1A		-0.9	-1.5	V
I_{CBO}	Collector cut-off current		V_{CB}=-120V; I_E=0			-1.0	μA
I_{EBO}	Emitter cut-off current		V_{EB}=-3V; I_C=0			-1.0	μA
h_{FE-1}	DC current gain		I_C=-5mA ; V_{CE}=-5V	35			
h_{FE-2}	DC current gain		I_C=-0.3A ; V_{CE}=-5V	60	150	320	
C_{OB}	Output capacitance		I_E=0 ; V_{CB}=-10V,f=1MHz		29		pF
f_T	Transition frequency		I_C=-0.2A ; V_{CE}=-5V		180		MHz

◆ **h_{FE-2} Classifications**

R	Q	P
60-120	100-200	160-320

PACKAGE OUTLINE

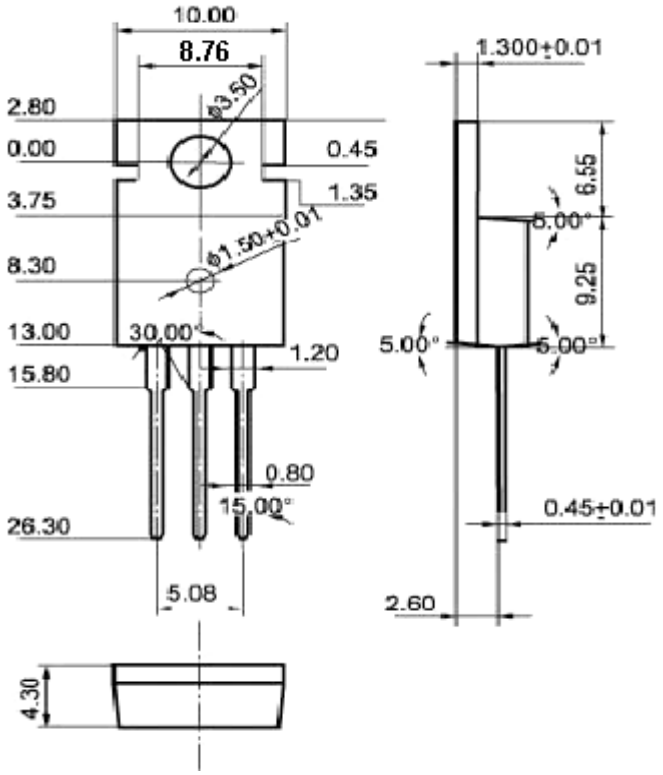


Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)